

N-Channel Power MOSFET

800V, 8A, 1.4Ω

Features

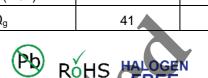
- Low $R_{DS(ON)}$ 1.4 Ω (Max.)
- Low gate charge typical @ 41nC (Typ.)
- Improve dV/dt capability

KEY PERFORMANCE PARAMETERS			
PARAMETER	VALUE UNI		
V_{DS}	800	V	
R _{DS(on)} (max)	1.4	Ω	
Q_g	41	nC	

APPLICATION

- **Power Supply**
- Lighting.





Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)				
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT
Drain-Source Voltage	V _{DS}	800		V
Gate-Source Voltage	V_{GS}	±30		V
Continuous Drain Current (Note 4) T _C = 25°C	l _D	8		А
T _C = 100°C		4.9		
Pulsed Drain Current (Note 2)	I _{DM}	32		Α
Total Power Dissipation @ T _C = 25°C	P _{DTOT}	250	40.3	W
Single Pulsed Avalanche Energy (Note 3)	E _{AS}	160		mJ
Single Pulsed Avalanche Current (Note 3)	I _{AS}	8		Α
Repetitive Avalanche Energy	E _{AR}	25		mJ
Peak Diode Recovery ^(Note 7)	dV/dt	4	.5	V
Operating Junction and Storage Temperature Range	T _J , T _{STG}	- 55 to	+150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT
Junction to Case Thermal Resistance	R _{eJC}	0.5 3.1		°C/W
Junction to Ambient Thermal Resistance	R _{OJA}	62.5		°C/W

Notes: R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\mbox{\scriptsize BJA}}$ shown below for single device operation on FR-4 PCB in still air.



ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						•
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	800			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2.0		4.0	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 800V, V_{GS} = 0V$	I _{DSS}			10	μΑ
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 4.0A$	R _{DS(ON)}		1.1	1.4	Ω
Forward Transconductance	$V_{DS} = 30V, I_{D} = 4.0A$	g _{fs}		7		S
Diode Forward Voltage	$I_{S} = 8A, V_{GS} = 0V$	V_{SD}			1.5	V
Dynamic (Note 5)						
Total Gate Charge	., ., ., ., ., ., .,	Q_g		41		
Gate-Source Charge	$V_{DS} = 640V, I_{D} = 8.0A,$ $V_{GS} = 10V$	Q _{gs}		10		nC
Gate-Drain Charge	V _{GS} = 10 V	Q_{gd}	<i>-</i> -	11		
Input Capacitance	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	\mathcal{C}_{iss}		1921		
Output Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1.0MHz$	Coss		146		pF
Reverse Transfer Capacitance		C _{rss}		12		
Gate Resistance	F = 1MHz, open drain	R_g		2.9		Ω
Switching (Note 6)						
Turn-On Delay Time		t _{d(on)}		133		
Turn-On Rise Time	$V_{DD} = 400V$,	t _r		30		
Turn-Off Delay Time	$R_{GEN} = 25\Omega$, $I_D = 8.0A$, $V_{GS} = 10V$,	t _{d(off)}		172		ns
Turn-Off Fall Time	10 = 0.071, VGS = 10 V,	t _f		37		
Source-Drain Diode (Note 4)	7					
Forward On Voltage	$I_S = 8.0A, V_{GS} = 0V$	V _{SD}		-	1.5	V
Reverse Recovery Time	$V_{GS} = 0V, I_{S} = 8A$	t _{rr}		479		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		5.5		μC

Notes:

- 1. Current limited by package.
- 2. Pulse width limited by the maximum junction temperature.
- 3. L = 5mH, $I_{AS} = 8A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$.
- 4. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%.
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.
- 7. $I_{SD} \le 8A$, $dI/dt \le 200A/uS$, $Vdd \le BV$, $Starting T_J = 25$ $^{\circ}C$.



ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM8N80CZ C0G	TO-220	50pcs / Tube
TSM8N80CI C0G	ITO-220	50pcs / Tube

Note:

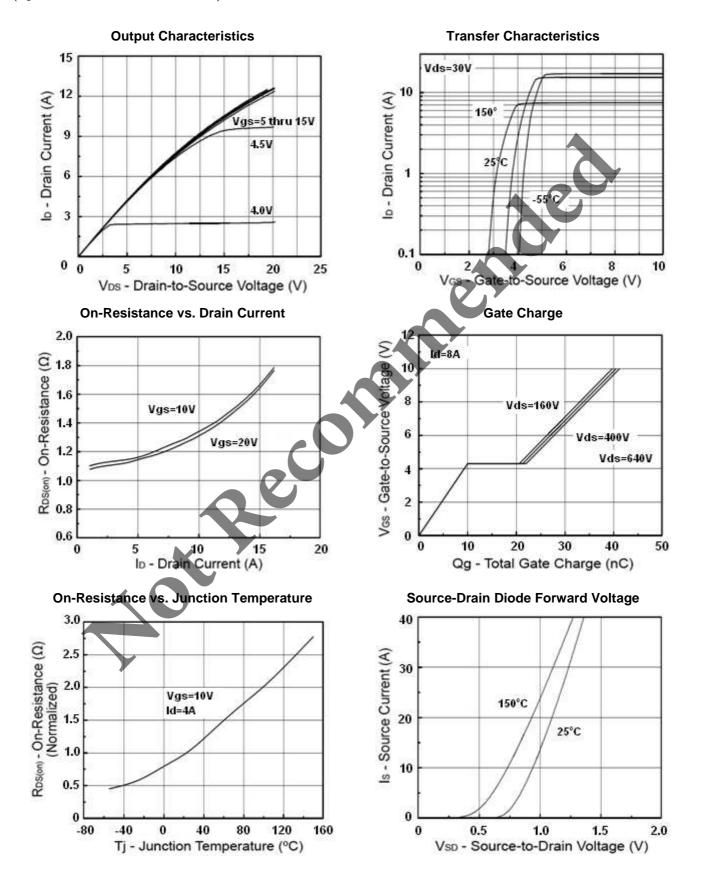
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition





CHARACTERISTICS CURVES

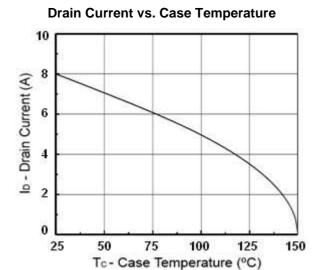
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

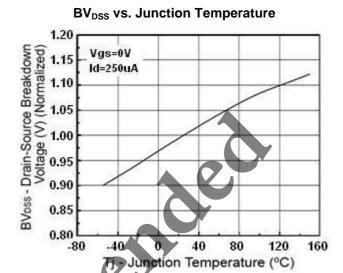


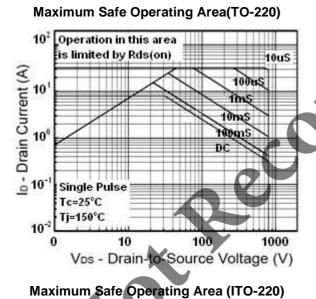


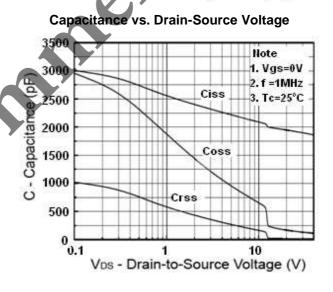
CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$









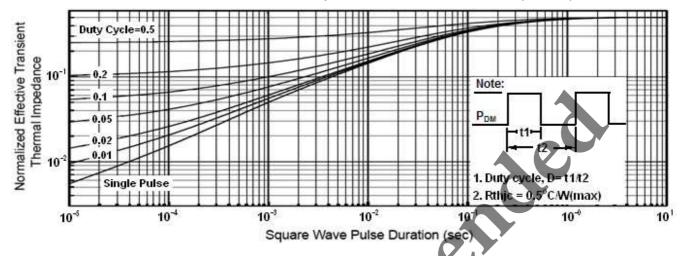
Vps - Drain-to-Source Voltage (V)



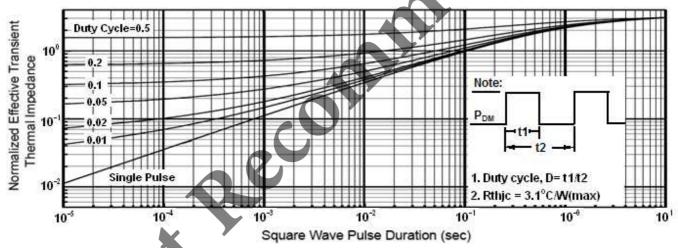
ELECTRICAL CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

Normalized Thermal Transient Impedance, Junction-to-Ambient (TO-220)

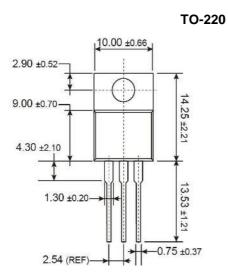


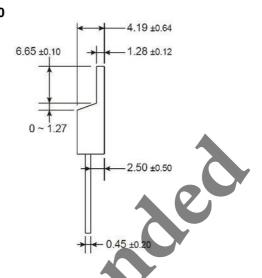
Normalized Thermal Transient Impedance, Junction-to-Ambient (ITO-220)





PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)





MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

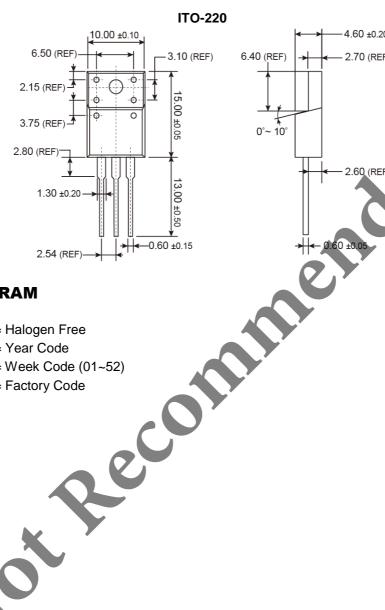
O =Jan P =Feb **Q** =Mar

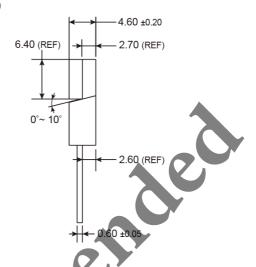
S =May T =Jun **U** =Jul

W =Sep X =Oct



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)





MARKING DIAGRAM



G = Halogen Free

= Year Code

WW = Week Code (01~52)

= Factory Code





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